

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**INFORMATION DISCLOSURE STATEMENT**

APPLICANT(S): Hiroyuki YOshida      DOCKET NO.: 09792909-6113  
SERIAL NO.: 10/524,749      GROUP ART UNIT: 2612  
DATE FILED: February 15, 2005      EXAMINER: Abul Kalam  
INVENTION: INSULATED GATE FIELD EFFECT TRANSISTOR AND METHOD OF  
MANUFACTURING SAME, AND IMAGE PICKUP DEVICE AND  
METHOD OF MANUFACTURING SAME

Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

S I R:

In accordance with the provisions of 37 C.F.R. § 1.56, Applicants request that citation and examination of the references identified on the attached PTO-SB08A form, in accordance with 37 C.F.R. §1.98, be made during the course of examination of the above-referenced application for United States Letters Patent. These references were cited in an Office Action issued on February 27, 2007, in connection with Japanese application no. JP2002-237838. Copies of the foreign references and machine translations are attached as is a copy of the Japanese office action.

Respectfully submitted by,

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